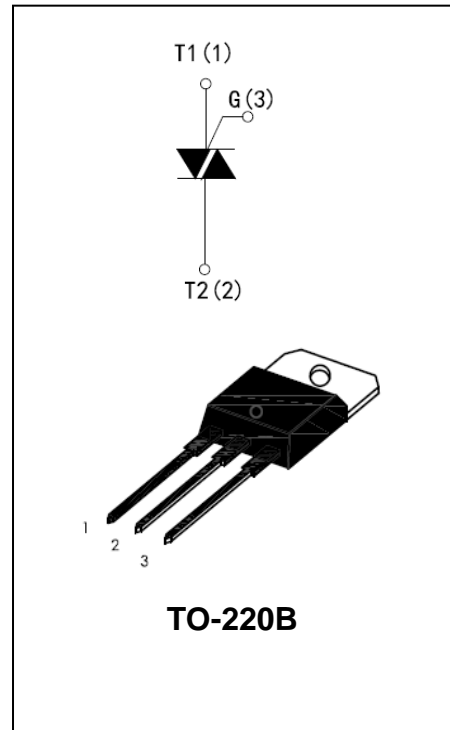




High current density due to double mesa technology; SIPOS and Glass Passivation. IPT1206-xx series are suitable for general purpose AC Switching. They can be used as an ON/OFF function In application such as static relays, heating regulation, Induction motor starting circuits... or for phase Control operation light dimmers, motor speed Controllers. IPT1206-xx series is 3 Quadrants triacs, This is specially recommended for use on inductive Loads..



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM} / V_{RRM}	600	V
V_{TM}	≤ 1.55	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage Junction Temperature Range	T_{stg}	-40 to +150	$^{\circ}C$
Operating Junction Temperature Range	T_j	-40 to +125	$^{\circ}C$
Repetitive Peak Off-state Voltage Repetitive Peak Reverse Voltage	V_{DRM} V_{RRM}	600 600	V
Non Repetitive Peak Off-state Voltage Non Repetitive Peak Reverse Voltage	V_{DSM} V_{RSM}	700 700	V
RMS on-state current (Full sine wave)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state Current (full cycle, $T_j = 25^{\circ}C$)	I_{TSM}	126 120	A
I^2t Value for fusing	I^2t	78	A^2s
Critical Rate of rise of on-state current $I_G = 2xI_{GT}$, $t_r \leq 100ns$, $f = 120Hz$, $T_j = 125^{\circ}C$	di / dt	50	A/us
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W

ELECTRICAL CHARACTERISTICS(T_j = 25 °C unless otherwise specified)

Symbol	Test Condition	Quadrant		IPT1206-xxB				Unit
				TE	SE	CE	BE	
I _{GT}	V _D = 12V R _L = 30Ω	I – II – III	MAX	5	10	35	50	mA
V _{GT}		I – II – III	MAX	1.3				V
V _{GD}	V _D =V _{DRM} , R _L =3.3KΩ, T _j = 125 °C	I – II – III	MIN	0.2				V
I _L	I _G = 1.2 I _{GT}	I – III	MAX	10	25	50	70	mA
		II		15	30	60	80	
I _H	I _T = 100mA		MAX	10	15	35	50	mA
dV/dt	V _D = 67% V _{DRM} gate open T _j = 125 °C		MIN	20	40	500	1000	V/us
(di/dt) _c	(dV/dt) c=0.1V/us T _j = 125 °C		MIN	3.5	6.5	-	-	A/ms
	(dV/dt) c=10V/us T _j = 125 °C			1.0	2.9	-	-	
	Without snubber T _j = 125 °C			-	-	6.5	12	

STATIC CHARACTERISTICS

Symbol	Test Conditions		Value(MAX)	Unit
V _{TM}	I _{TM} = 5.5A, t _p = 380uS	T _j = 25 °C	1.6	V
I _{DRM}	V _D = V _{DRM}	T _j = 25 °C	5	uA
I _{RRM}	V _R = V _{RRM}	T _j = 125 °C	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	1.4	°C/W

Fig. 1: Maximum power dissipation versus RMS on-state current(full cycle)

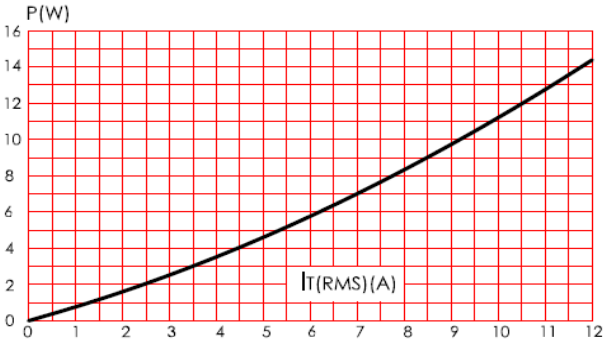


Fig. 2: RMS on-state current versus case temperature(full cycle)

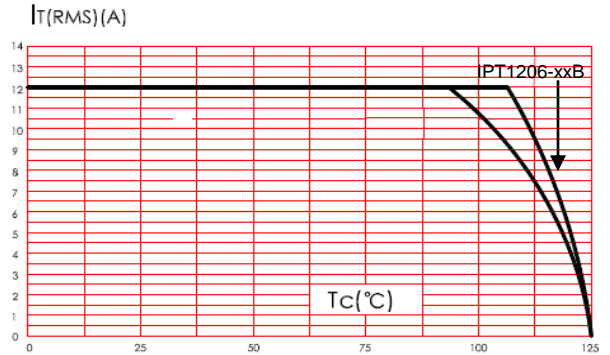


Fig. 3: on-state characteristics (maximum values)

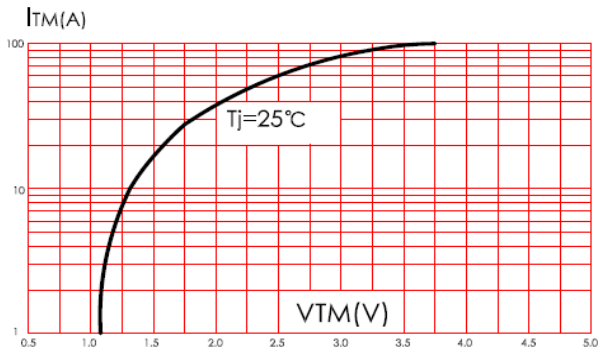


Fig. 4: Surge peak on-state current versus number of cycles

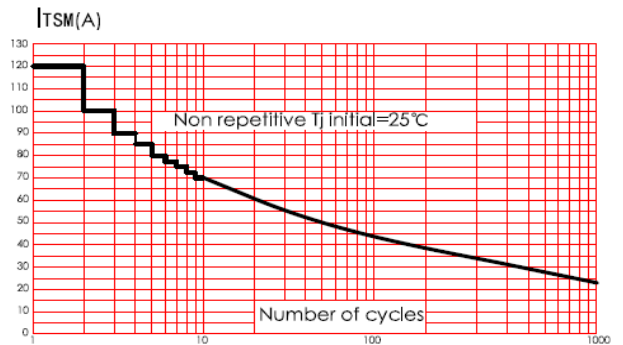


Fig. 5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$

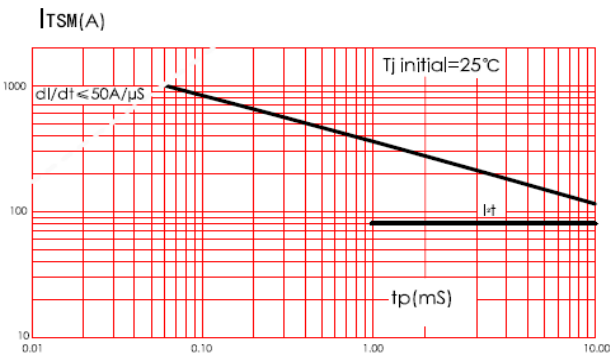


Fig. 6: Relative variation of gate trigger current, holding current and latching current versus junction temperature(typical values)

